

Silicon Diode

BY459X-1500S

1500V/10A

DATASHEET

OEM – Philips

Source: Philips Databook 1999

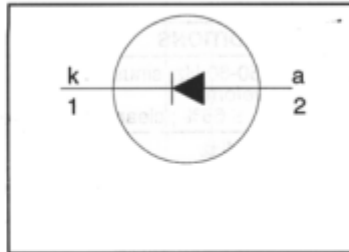
Damper diode fast, high-voltage

BY459X-1500, BY459X-1500S

FEATURES

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- High thermal cycling performance
- Isolated mounting tab

SYMBOL



QUICK REFERENCE DATA

$V_R = 1500$ V
$V_F \leq 1.2$ V / 1.25 V
$I_{F(\text{peak})} = 12$ A (f = 48 kHz)
$I_{F(\text{peak})} = 10$ A (f = 82 kHz)
$I_{FSM} \leq 100$ A
$t_r \leq 350$ ns / 220 ns

GENERAL DESCRIPTION

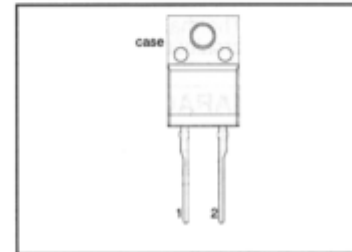
Glass-passivated double diffused rectifier diode featuring fast forward recovery and low forward recovery voltage. The device is intended for use in HDTV receivers and multi-sync monitor horizontal deflection circuits.

The BY459X series is supplied in the conventional leaded SOD113 package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode
tab	isolated

SOD113



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RSM}	Peak non repetitive reverse voltage		-	1500	V
V_{RRM}	Peak repetitive reverse voltage		-	1500	V
V_{RWM}	Crest working reverse voltage		-	1300	V
$I_{F(\text{peak})}$	Peak working forward current	f = 48 kHz;	-	-1500	A
		f = 82 kHz;	-	12	A
I_{FRM}	Peak repetitive forward current	t = 100 μ s	-	100	A
$I_{F(\text{RMS})}$	RMS forward current		-	30	A
I_{FSM}	Peak non-repetitive forward current	t = 10 ms	-	100	A
		t = 8.3 ms sinusoidal; $T_j = 150$ °C prior to surge; with reapplied $V_{RWM(\text{max})}$	-	110	A
T_{stg}	Storage temperature		-40	150	°C
T_j	Operating junction temperature		-	150	°C

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ISOLATION LIMITING VALUE & CHARACTERISTIC

$T_{ns} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	R.M.S. isolation voltage from both terminals to external heatsink	$f = 50\text{-}60\text{ Hz}$; sinusoidal waveform; R.H. $\leq 65\%$; clean and dustfree	-		2500	V
C_{isol}	Capacitance from both terminals to external heatsink	$f = 1\text{ MHz}$	-	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\text{-}hs}$	Thermal resistance junction to heatsink	with heatsink compound	-	-	4.8	K/W
$R_{th\text{-}a}$	Thermal resistance junction to ambient	without heatsink compound in free air.	-	55	5.9	K/W

STATIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	TYP.		MAX.		UNIT
			1500	1500S	1500	1500S	
V_F	Forward voltage	BY459X- $I_F = 6.5\text{ A}$ $I_F = 6.5\text{ A}; T_j = 125\text{ }^{\circ}\text{C}$	0.95	1.05	1.30	1.35	V
I_R	Reverse current	$V_R = 1300\text{ V}$ $V_R = 1300\text{ V}; T_j = 125\text{ }^{\circ}\text{C}$	0.85	0.95	1.20	1.25	V
			-	250	-	250	μA
			-	1	-	1	mA

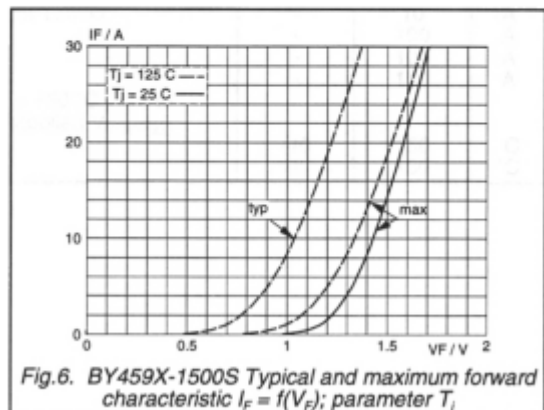
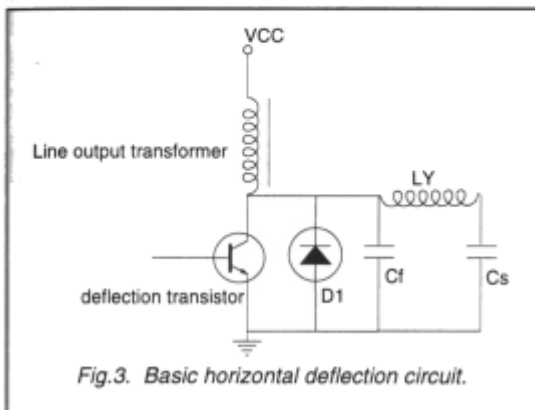
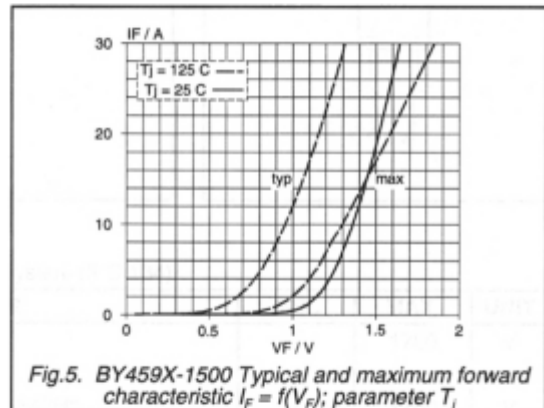
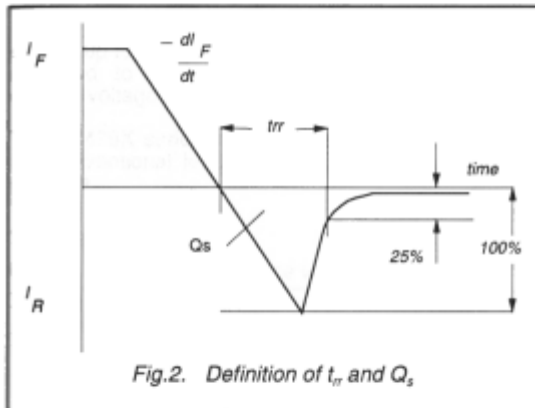
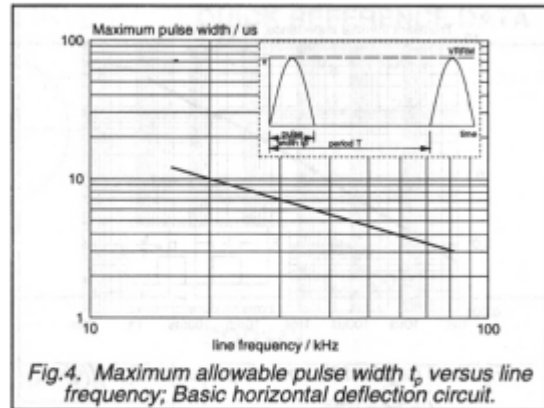
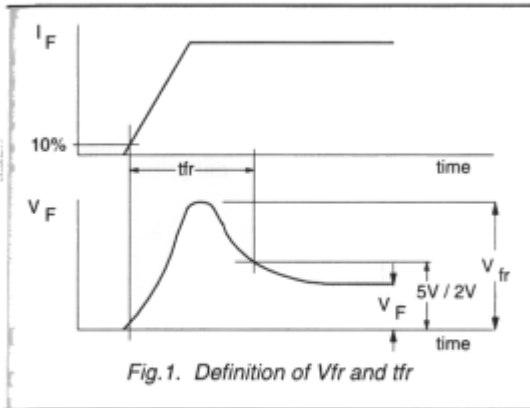
DYNAMIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	TYP.		MAX.		UNIT
			1500	1500S	1500	1500S	
t_{rr}	Reverse recovery time	BY459X- $I_F = 1\text{ A}, V_R \geq 30\text{ V}$	0.25	0.17	0.35	0.22	μs
Q_s	Reverse recovery charge	$I_F = 2\text{ A}, -di_F/dt = 20\text{ A}/\mu\text{s}$	2.0	0.70	3.0	0.95	μC
V_{fr}	Peak forward recovery voltage	$I_F = 6.5\text{ A}, di_F/dt = 50\text{ A}/\mu\text{s}$	8.0	11.0	14.0	19.0	V
t_{fr}	Forward recovery time	$I_F = 6.5\text{ A}, di_F/dt = 50\text{ A}/\mu\text{s}$	170	200	250	300	ns

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